

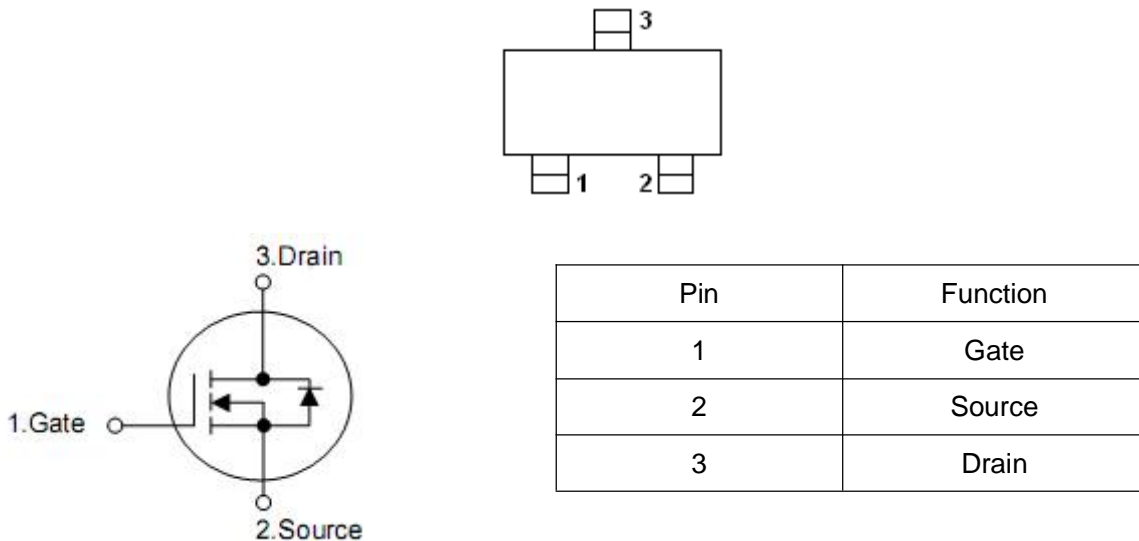
1. Description

The KIA3400 uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. Standard Product KIA3400 is Pb-free (meets ROHS & Sony 259 specifications). KIA3400 is a Green Product ordering option. KIA3400 is electrically identical.

2. Features

- n $V_{DS}(V)=30V$
- n $I_D=4.8A(V_{GS}=10V)$
- n $R_{DS(on)}<34m\Omega(V_{GS}=10V, I_D=4.8A)$
- n $R_{DS(on)}<40m\Omega(V_{GS}=4.5V, I_D=4.0A)$
- n $R_{DS(on)}<56m\Omega(V_{GS}=2.5V, I_D=3.5A)$

3. Symbol



4. Absolute maximum ratings

(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units	
Drain-source voltage	V _{DS}	30	V	
Gate-source voltage	V _{GS}	±12	V	
Continuous drain current ^A T _A =25°C	I _D	4.8	A	
Pulsed drain current ^B	I _{DM}	30	A	
Total power dissipation ^A	P _D	T _A =25 °C	1.4	W
		T _A =70°C	1	W
Junction and storage temperature range	T _J , T _{STG}	-55 to 150	°C	

5. Thermal characteristics

Parameter	Symbol	Typ	Max	Unit
Maximum junction-ambient ^A (t≤10s)	R _{θJA}	65	90	°C/W
Maximum junction-ambient ^A	R _{θJA}	85	125	°C/W
Maximum junction-Lead ^C	R _{θJL}	43	60	°C/W

6. Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=25V, V_{GS}=0V$	-	-	1	μA
Gate- body leakage current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6	-	-	V
On state drain current	$I_{D(on)}$	$V_{GS}=4.5V, V_{DS}=5V$	30	-	-	A
Static drain-source on-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=4.8A$	-	-	34	m Ω
		$V_{GS}=4.5V, I_D=4.0A$	-	-	40	
		$V_{GS}=2.5V, I_D=3.5A$	-	-	56	
Forward transconductance	g_{fs}	$V_{DS}=5V, I_D=4.8A$	10	15	-	S
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=1A$	-	0.71	1.2	V
Maximum body-diode continuous current	I_S		-	-	2.5	A
Input capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $f=1\text{MHz}$	-	823	1030	pF
Output capacitance	C_{oss}		-	99	-	
Reverse transfer capacitance	C_{rss}		-	77	-	
Gate resistance	R_g	$V_{DS}=0V,$ $V_{GS}=0V, f=1\text{MHz}$	-	1.2	3.6	Ω
Total gate charge	Q_g	$V_{DS}=15V, V_{GS}=4.5V$ $I_D=5.8A$	-	9.7	12	nC
Gate-source charge	Q_{gs}		-	1.6	-	
Gate-drain charge	Q_{gd}		-	3.1	-	
Turn-on delay time	$t_{d(on)}$	$V_{DS}=15V, R_L=2.7\Omega,$ $R_G=3\Omega, V_{GS}=10V$	-	3.3	5	ns
Rise time	t_r		-	4.8	7	
Turn-off delay time	$t_{d(off)}$		-	26.3	40	
Fall time	t_f		-	4.1	6	
Reverse recovery time	t_{rr}	$I_F=5A, di/dt=100A/\mu s,$	-	16	20	nS
Reverse recovery charge	Q_{rr}		-	8.9	12'	nC

Note:A.The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.Copper,in a still air environment with $T_A=25^\circ\text{C}$.The value in any given application depends on the user's specific board design.The current rating is based on the $t \leq 10s$ thermal resistance rating.

B.Repetitive rating,pulse width limited by junction temperature.

C.The $R_{\theta JA}$ the sum of the thermal inpedence from junction to lead $R_{\theta j l}$ and lead to ambient.

D.The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses,duty cycle 0.5% max.

E.These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper,in a still air environment with $T_A=25^\circ\text{C}$.The SOA curve provides a single pulse rating.

7. Test circuits and waveforms

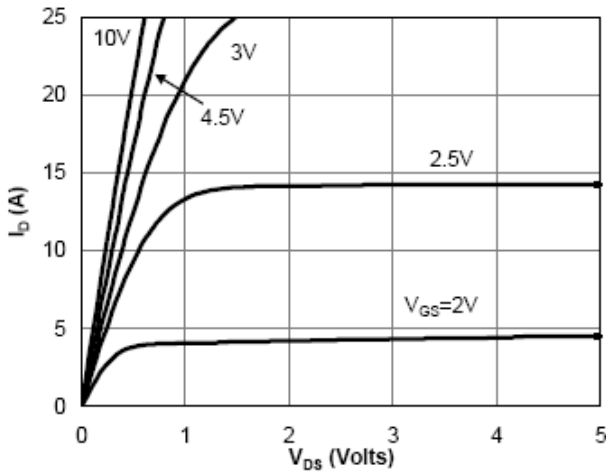


Fig 1: On-Region Characteristics

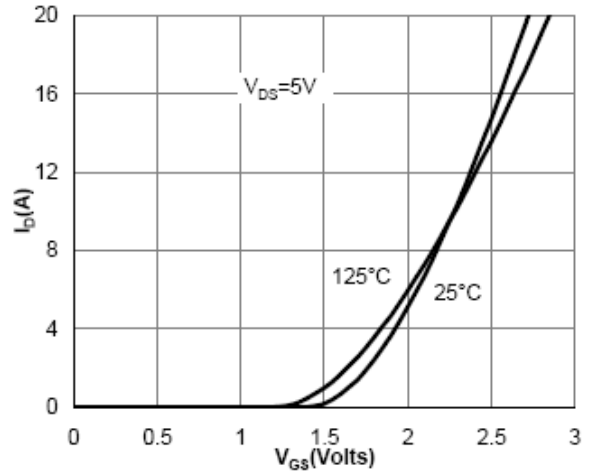


Figure 2: Transfer Characteristics

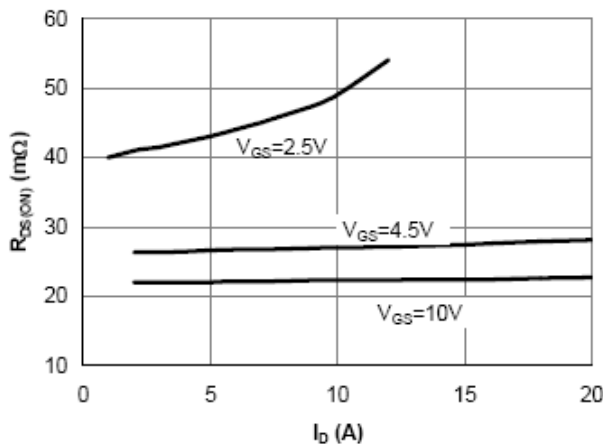


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

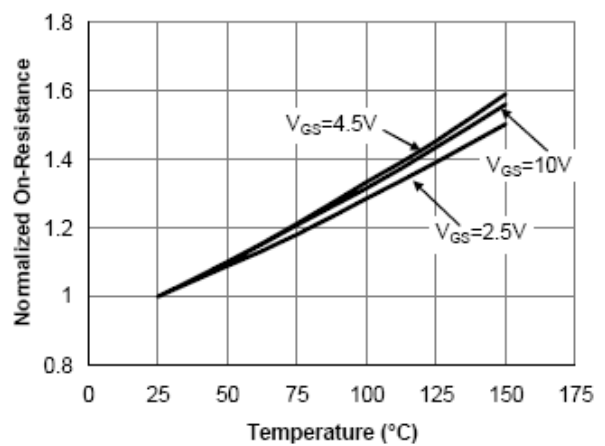


Figure 4: On-Resistance vs. Junction Temperature

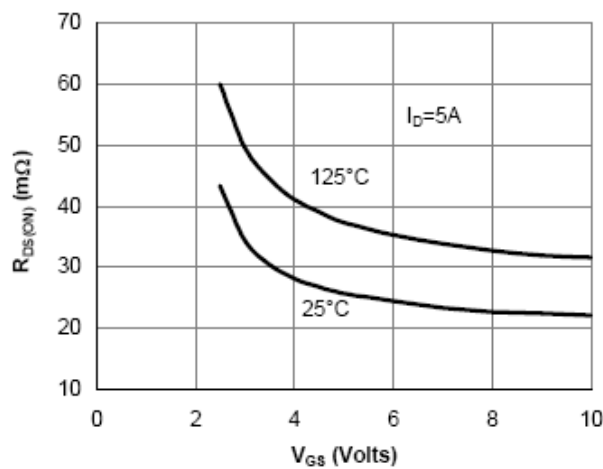


Figure 5: On-Resistance vs. Gate-Source Voltage

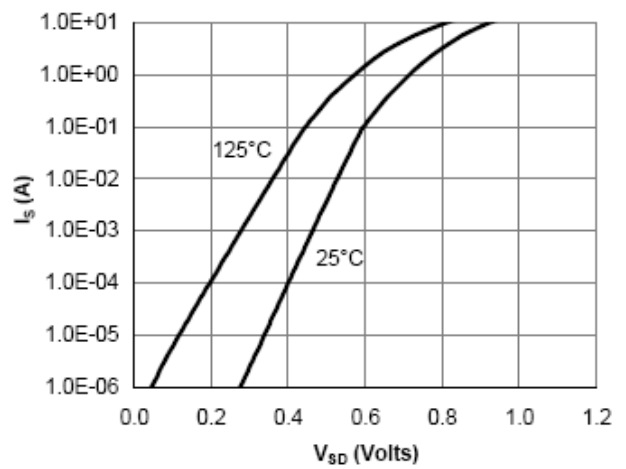


Figure 6: Body-Diode Characteristics

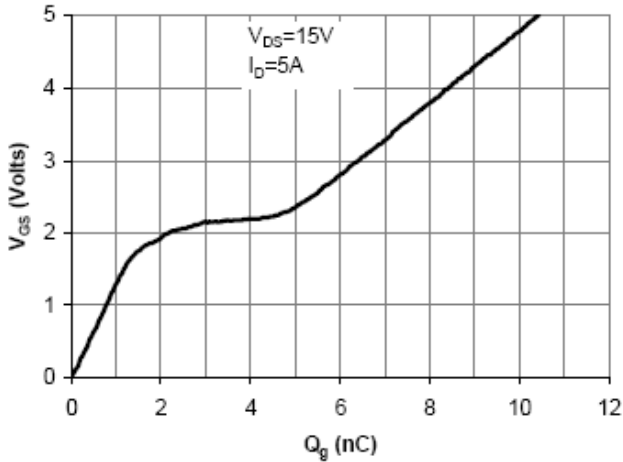


Figure 7: Gate-Charge Characteristics

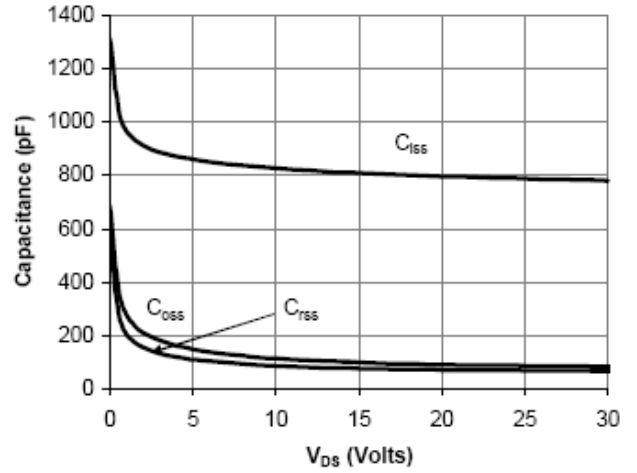


Figure 8: Capacitance Characteristics

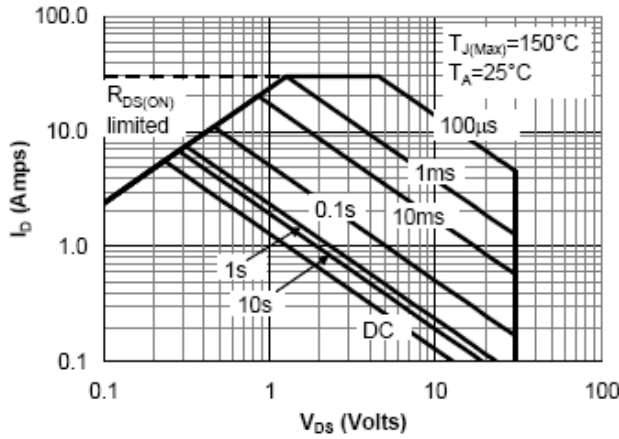


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

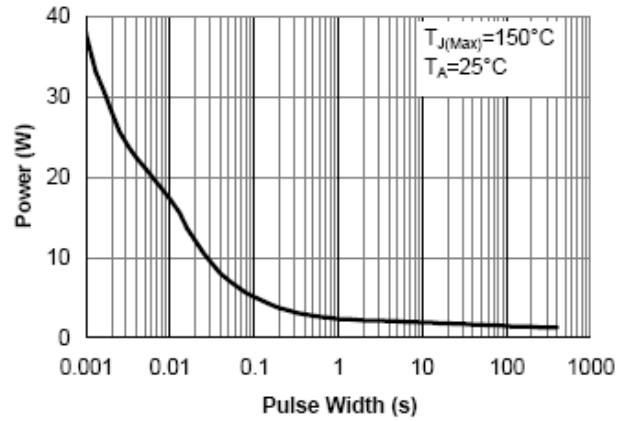


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

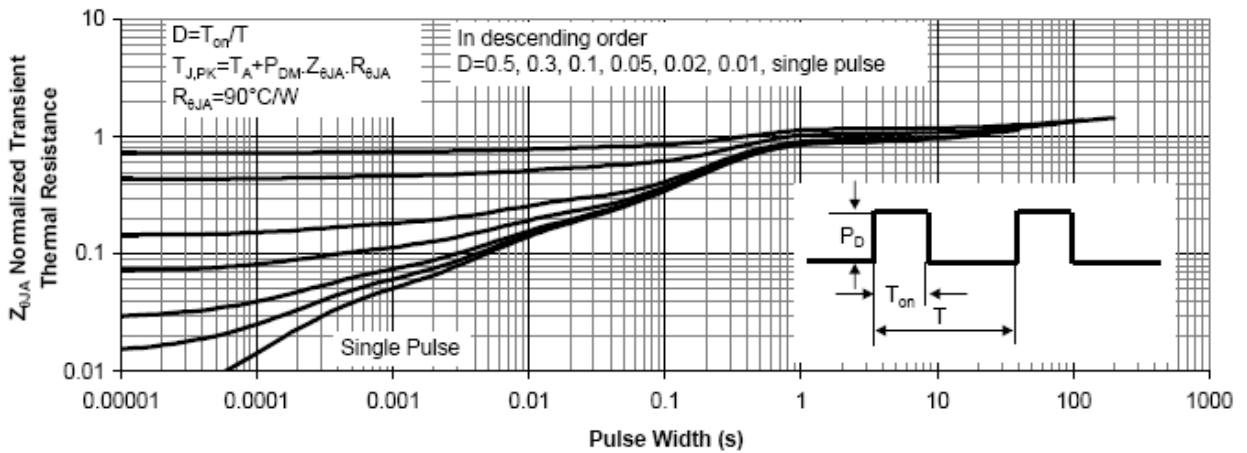


Figure 11: Normalized Maximum Transient Thermal Impedance

